

SEMITOP[®]4

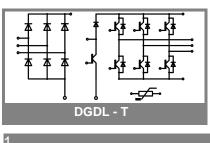
3-phase bridge rectifier + brake chopper + 3-phase bridge inverter **SK 50 DGDL 12T4 T**

Target Data

Features

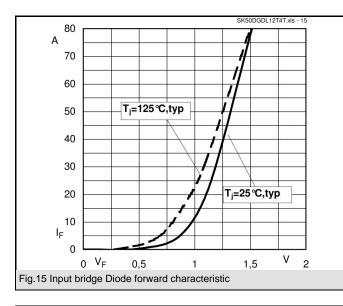
- One screw mounting module
- Fully compatible with SEMITOP[®]1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench4 IGBT technology
- CAL4 technology free-wheeling diode
- Integrated NTC temperature sensor

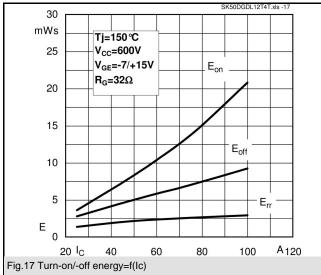
1) $V_{CE,sat}$, V_F = chip level value

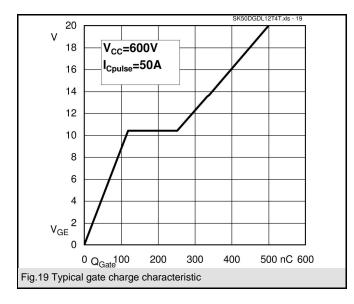


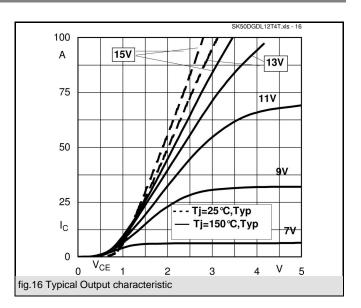
Absolute	Maximum Ratings	Ts = 25 °C, unless otherwise specified						
Symbol	Conditions	Values	Units					
IGBT - Inverter.For IGBT chopper maximum ratings, please refer to SK35DGDL12T4T								
V _{CES}		1200	V					
I _C	T _s = 25 (70) °C	75 (60)	A					
I _{CRM}	$I_{CRM} = 3 \times I_{Cnom}$, $t_p = 1 \text{ ms}$	150	А					
V _{GES}		± 20	V					
T _j		-40 +175	°C					
Diode - Inverter, Chopper								
I _F	T _s = 25 (70) °C	60 (45)	Α					
I _{FRM}	$I_{FRM} = 2xI_{Fnom}, t_p = 1 \text{ ms}$	150	А					
Т _ј		-40 +150	°C					
Rectifier		· ·	•					
V _{RRM}		1600	V					
I _F	T _s = 70 °C	61	Α					
I _{FSM} / I _{TSM}	t _p = 10 ms , sin 180 ° ,T _j = 25 °C	700	Α					
I ² t	t _p = 10 ms , sin 180 ° ,T _j = 25 °C	2400	A²s					
Т _ј		-40 +175	°C					
T _{sol}	Terminals, 10 s	260	°C					
T _{stg}		-40 +125	°C					
V _{isol}	AC, 1 min. / 1 s	2500 / 3000	V					

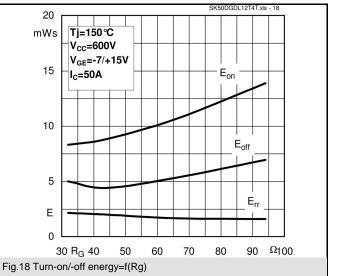
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Symbol	Conditions	min.	typ.	max.	Unit
	verter. For IGBT chopper electr	ical charac	cteristics,	please ref	er to
SK35DGI					
V _{CEsat}	I _C = 50 A, T _j = 25 (150) °C		,	2,05 (2,45)	V
V _{GE(th)}	$V_{GE} = V_{CE}, I_{C} = 1,7 \text{ mA}$	5	5,8	6,5	V
V _{CE(TO)}	T _j = 25 °C (150) °C		1,1 (1)	1,3 (1,2)	V
r _T	T _j = 25 °C (150) °C		15 (24)		mΩ
Cies	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		2,77		nF
C _{oes}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,2		nF
C _{res}	V _{CE} = 25 V _{GE} = 0 V, f = 1 MHz		0,16		nF
R _{th(j-s)}	per IGBT		0,65		K/W
t _{d(on)}	under following conditions		63		ns
t, ` ´	$V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$		65		ns
t _{d(off)}	I _C = 50 A, T _j = 150 °C		521		ns
t _r	$R_{Gon} = R_{Goff} = 32 \ \Omega$		80		ns
E _{on}	inductive load		8,3		mJ
E _{off}			5		mJ
Diode - Ir	nverter,Chopper	•			
$V_F = V_{EC}$	$I_{\rm F} = 50 \text{ A}, T_{\rm i} = 25(150) ^{\circ}{\rm C}$		2.22 (2.18)	2,54 (2,5)	V
V _(TO)	T _i = 25 °C (150) °C			1,5 (1,1)	V
r _T	T _i = 25 °C (150) °C		18,4 (25,6)		mΩ
R _{th(j-s)}	per diode		0,97		K/W
I _{RRM}	under following conditions		30		Α
Q _{rr}	$I_{\rm F} = 50 \text{ A}, V_{\rm B} = 300 \text{ V}$		7,2		μC
E _{rr}	$V_{GE} = 0 V, T_{i} = 150 °C$		2,15		mJ
11	di _{F/dt} = 920 A/µs		, -		
Diode - R					
V _F	I _F = 50 A, T _i = 25(150) °C	1	1,1		V
V _(TO)	$T_i = 150 \text{°C}$		0,8		v
r _T	T _i = 150 °C		6		mΩ
R _{th(j-s)}	per diode		0,9		K/W
	tur sensor		- , -		
R _{ts}	5 %, T _r = 25 (100) °C	Í	5000(493)		Ω
			5000(+00)		32
Mechanio w		1	60		g
M _s	Mounting torque		3,5		9 Nm
	7-04-2009 DIL		,	by SEMIK	

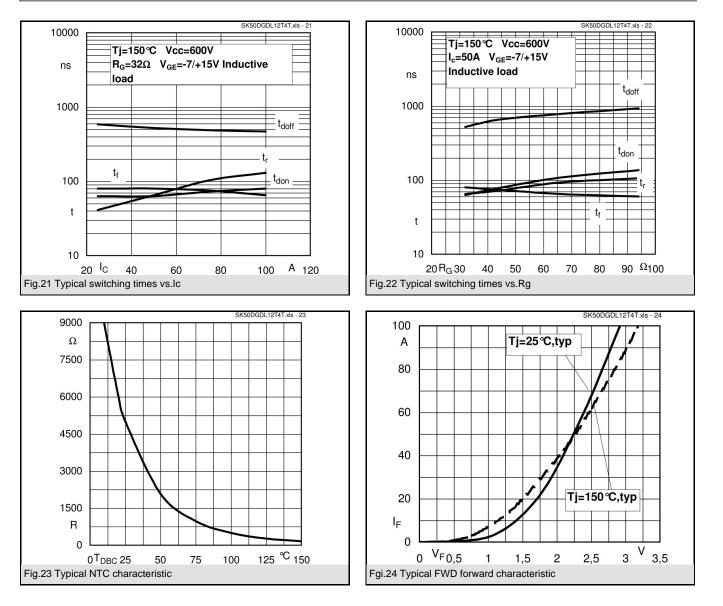




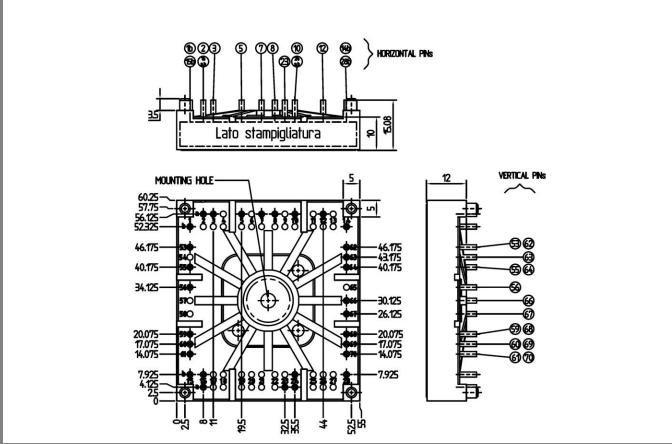


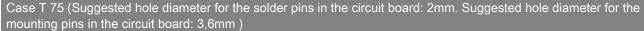


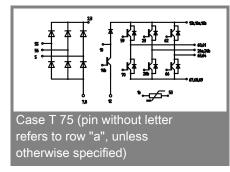




Dimensions in mm







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.